



PD4N90

900V N-Channel MOSFET

Lead Free Package and Finish

General Features

- Proprietary New Planar Technology
- $R_{DS(ON),typ.} = 3.6 \Omega @ V_{GS} = 10V$
- Low Gate Charge Minimize Switching Loss
- Fast Recovery Body Diode

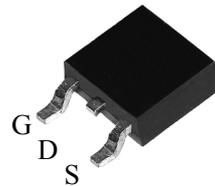
Applications

- CRT, TV/Monitor
- Other Applications

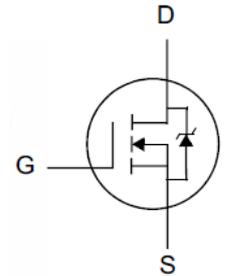
Ordering Information

Part Number	Package	Marking
PD4N90	TO-252	PD4N90T2

BV_{DSS}	$R_{DS(ON),typ.}$	I_D
900V	3.6Ω	4A



TO-252



Package No to Scale

Absolute Maximum Ratings

$T_c = 25^\circ C$ unless otherwise specified

Symbol	Parameter	PD4N90	Unit
V_{DSS}	Drain-to-Source Voltage ^[1]	900	V
V_{GSS}	Gate-to-Source Voltage	± 30	
I_D	Continuous Drain Current	4	A
$I_D @ T_c = 100^\circ C$	Continuous Drain Current @ $T_c = 100^\circ C$	Figure 3	
I_{DM}	Pulsed Drain Current at $V_{GS} = 10V$ ^[2]	16	
E_{AS}	Single Pulse Avalanche Energy	650	mJ
dv/dt	Peak Diode Recovery dv/dt ^[3]	5.0	V/ns
P_D	Power Dissipation	90	W
	Derating Factor above $25^\circ C$	0.72	W/ $^\circ C$
T_L T_{PAK}	Maximum Temperature for Soldering Leads at 0.063in (1.6mm) from Case for 10 seconds, Package Body for 10 seconds	300 260	$^\circ C$
T_J & T_{STG}	Operating and Storage Temperature Range	-55 to 150	

Caution: Stresses greater than those listed in the "Absolute Maximum Ratings" may cause permanent damage to the device.

Thermal Characteristics

Symbol	Parameter	PD4N90	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	1.38	$^\circ C/W$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	75	

Electrical Characteristics

OFF Characteristics $T_J = 25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	900	--	--	V	$V_{GS}=0V, I_D=250\mu A$
I_{DSS}	Drain-to-Source Leakage Current	--	--	1	uA	$V_{DS}=900V, V_{GS}=0V$
		--	--	100		$V_{DS}=720V, V_{GS}=0V, T_J=125^\circ\text{C}$
I_{GSS}	Gate-to-Source Leakage Current	--	--	+100	nA	$V_{GS}=+30V, V_{DS}=0V$
		--	--	-100		$V_{GS}=-30V, V_{DS}=0V$

ON Characteristics

 $T_J = 25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
$R_{DS(ON)}$	Static Drain-to-Source On-Resistance ^[4]	--	3.6	4.8	Ω	$V_{GS}=10V, I_D=2.0A$
$V_{GS(TH)}$	Gate Threshold Voltage	2.0	--	4.0	V	$V_{DS}=V_{GS}, I_D=250\mu A$
gfs	Forward Transconductance ^[4]	--	5.5	--	S	$V_{DS}=15V, I_D=4.0A$

Dynamic Characteristics

Essentially independent of operating temperature

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
C_{iss}	Input Capacitance	--	490	--	pF	$V_{GS}=0V, V_{DS}=25V, f=1.0\text{MHz}$
C_{rSS}	Reverse Transfer Capacitance	--	25	--		
C_{oss}	Output Capacitance	--	50	--		
Q_g	Total Gate Charge	--	16	--	nC	$V_{DD}=400V, I_D=4A, V_{GS}=0 \text{ to } 10V$
Q_{gs}	Gate-to-Source Charge	--	3.0	--		
Q_{gd}	Gate-to-Drain (Miller) Charge	--	6.0	--		

Resistive Switching Characteristics

Essentially independent of operating temperature

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
$t_{d(ON)}$	Turn-on Delay Time	--	10	--	ns	$V_{DD}=400V, I_D=4A, V_{GS}=10V, R_G=12\Omega$
t_{rise}	Rise Time	--	10	--		
$t_{d(OFF)}$	Turn-Off Delay Time	--	30	--		
t_{fall}	Fall Time	--	15	--		



Source-Drain Body Diode Characteristics

T_J=25°C unless otherwise specified

Symbol	Parameter	Min	Typ.	Max.	Unit	Test Conditions
I _{SD}	Continuous Source Current ^[4]	--	--	4.0	A	Integral PN-diode in MOSFET
I _{SM}	Pulsed Source Current ^[4]	--	--	16		
V _{SD}	Diode Forward Voltage	--	--	1.5	V	I _S =4.0A, V _{GS} =0V
trr	Reverse recovery time	--	135	--	ns	V _{GS} =0V, I _F =4.0A, di _F /dt=100A/μs
Qrr	Reverse recovery charge	--	446	--	nC	

Note:

-
- [1] T_J=+25°C to +150°C
 - [2] Repetitive rating; pulse width limited by maximum junction temperature.
 - [3] I_{SD}= 4A di/dt < 100 A/μs, V_{DD} < BV_{DSS}, T_J=+150°C.
 - [4] Pulse width≤380μs; duty cycle≤2%.

Typical Characteristics

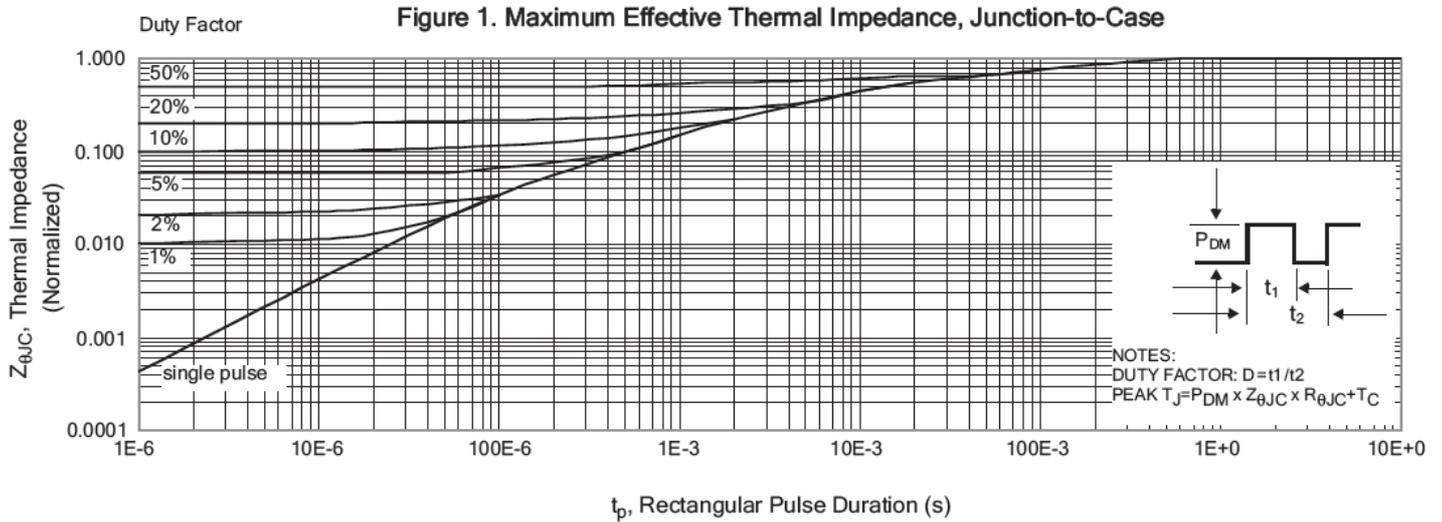


Figure 2 . Max. Power Dissipation vs Case Temperature

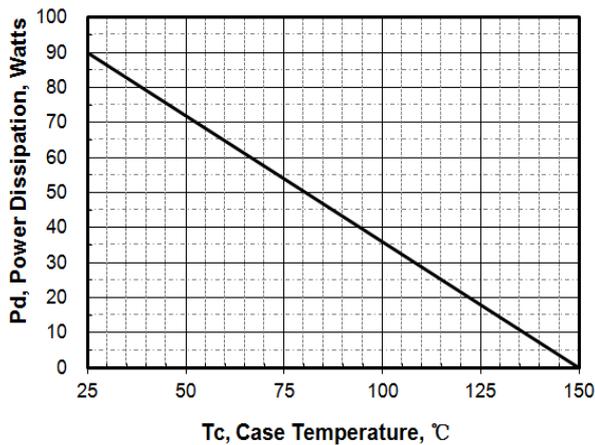


Figure 3. Maximum Continuous Drain Current vs Case Temperature

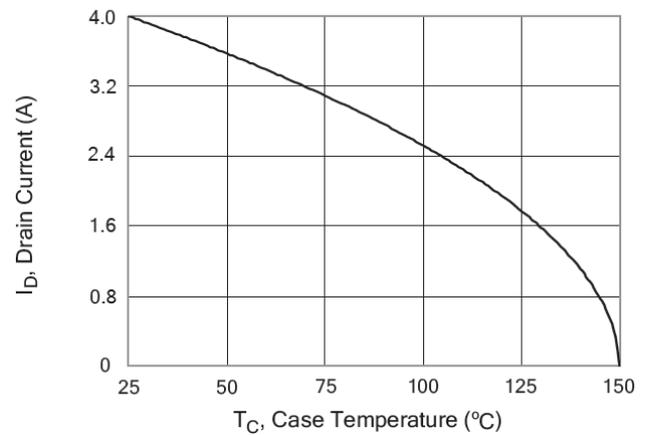


Figure 4. Typical Output Characteristics

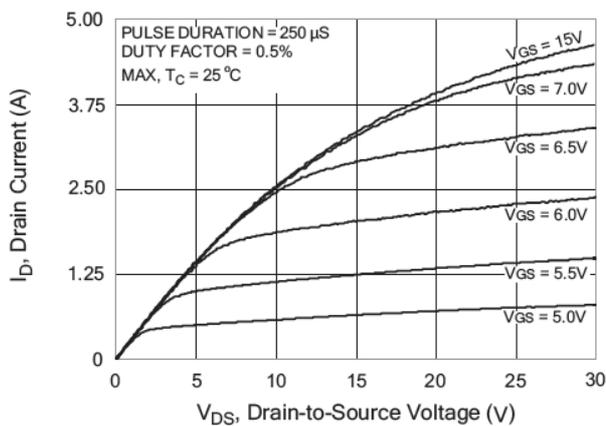
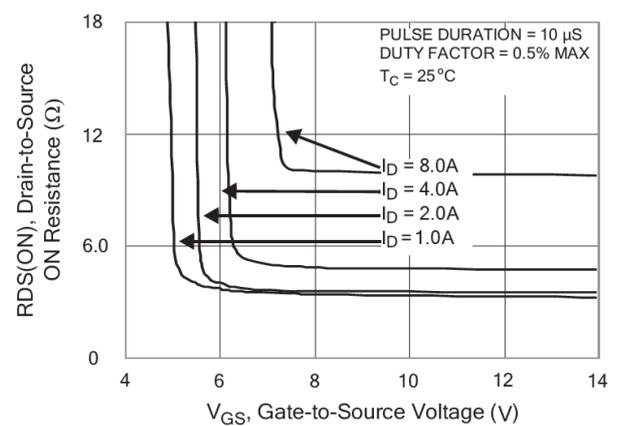


Figure 5. Typical Drain-to-Source ON Resistance vs Gate Voltage and Drain Current



Typical Characteristics(Cont.)

Figure 6. Maximum Peak Current Capability

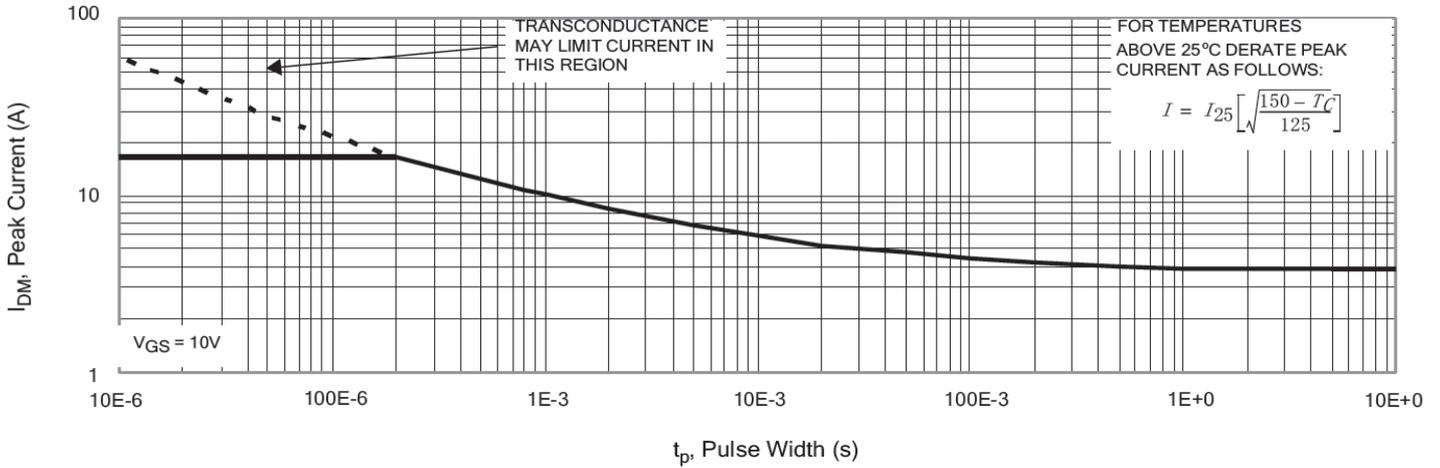


Figure 7. Typical Transfer Characteristics

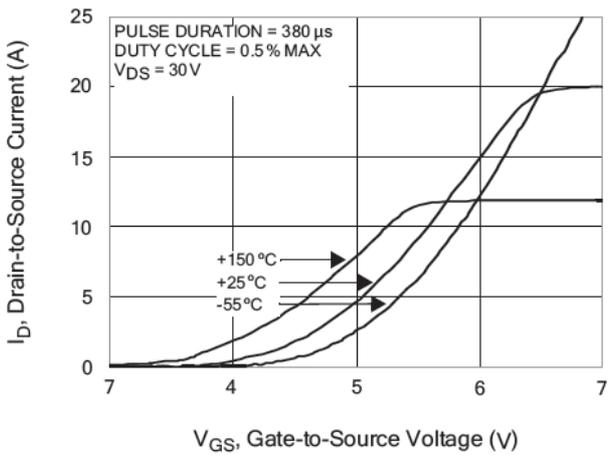


Figure 8. Unclamped Inductive Switching Capability

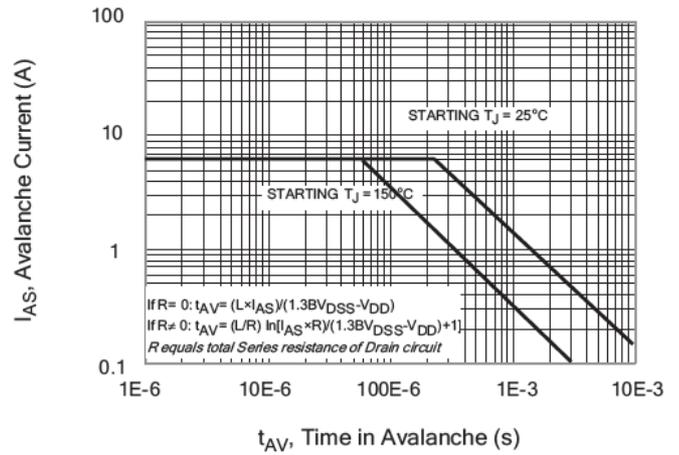


Figure 9. Typical Drain-to-Source ON Resistance vs Drain Current

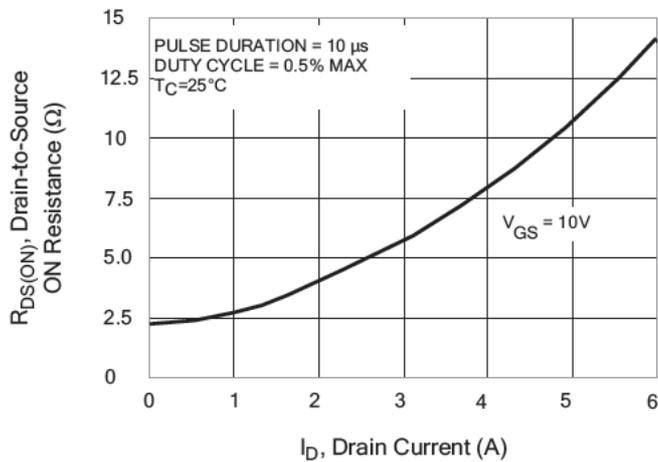
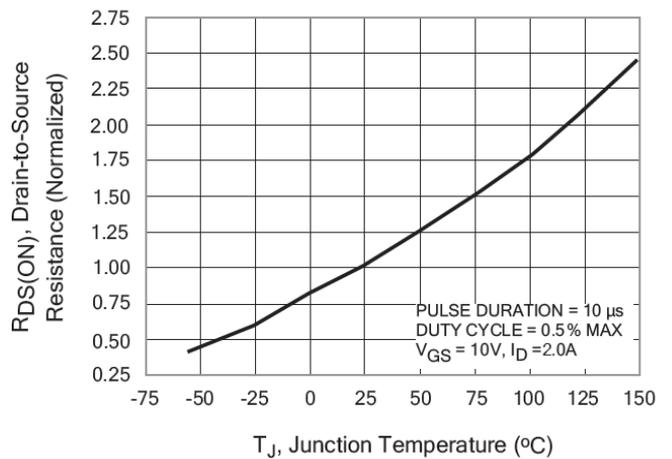


Figure 10. Typical Drain-to-Source ON Resistance vs Junction Temperature



Typical Characteristics(Cont.)

Figure 11. Typical Breakdown Voltage vs Junction Temperature

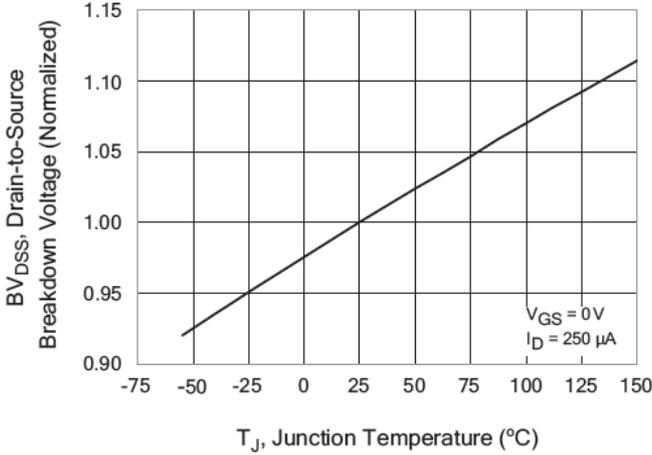


Figure 12. Typical Threshold Voltage vs Junction Temperature

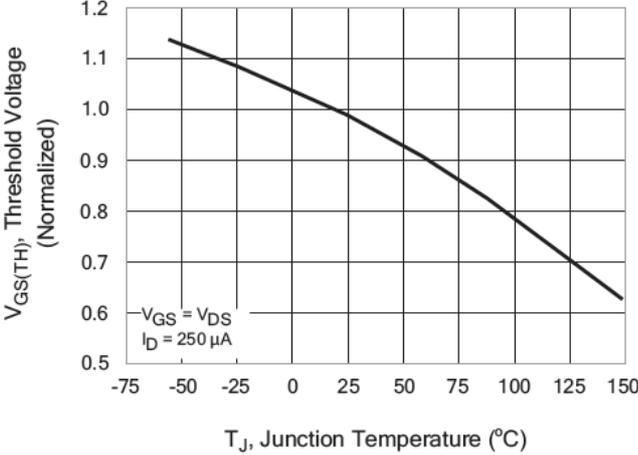


Figure 13. Maximum Safe Operating Area

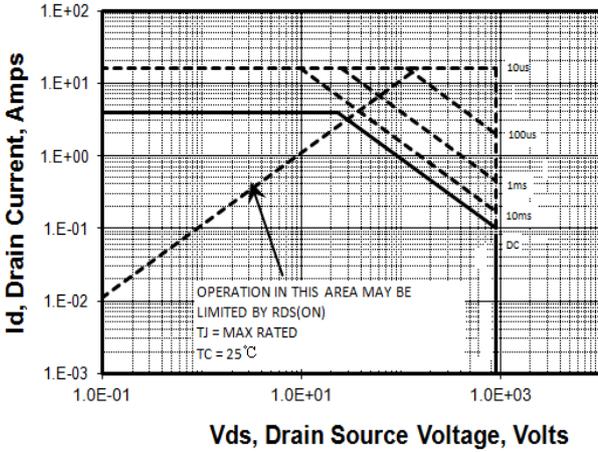


Figure 14. Typical Capacitance vs Drain-to-Source Voltage

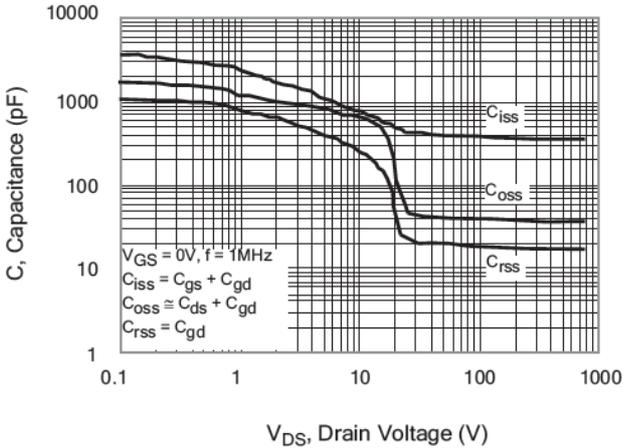


Figure 15. Typical Gate Charge vs Gate-to-Source Voltage

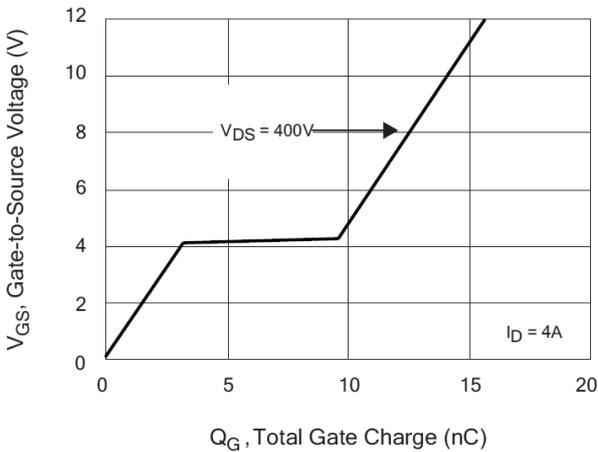
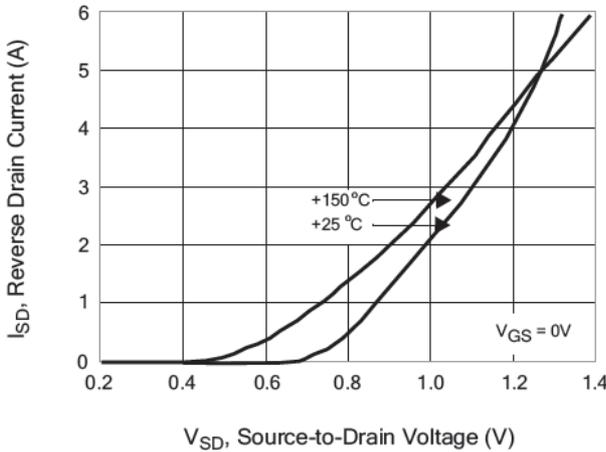


Figure 16. Typical Body Diode Transfer Characteristics



Test Circuits and Waveforms

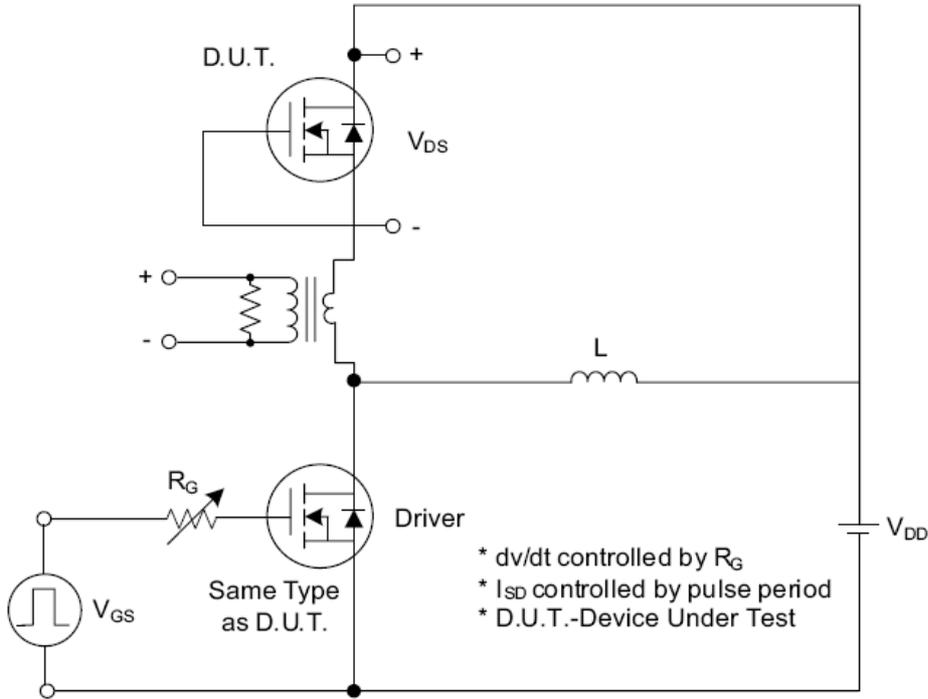


Fig. 1.1 Peak Diode Recovery dv/dt Test Circuit

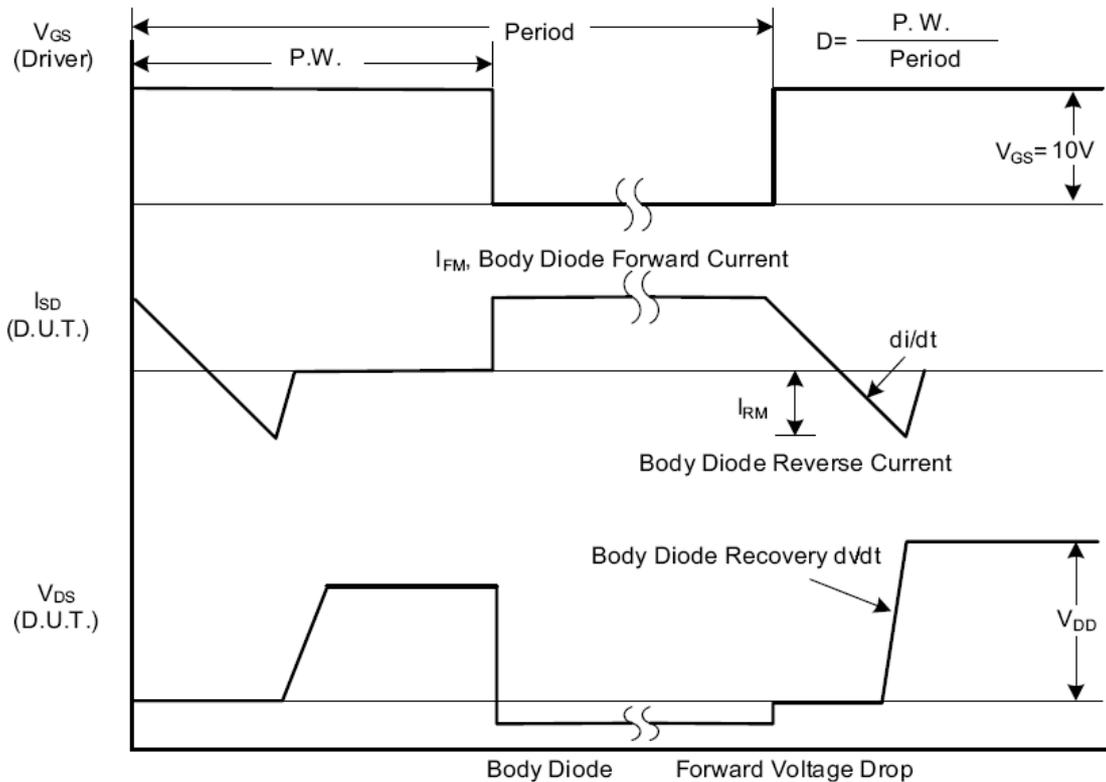


Fig. 1.2 Peak Diode Recovery dv/dt Waveforms

Test Circuits and Waveforms (Cont.)

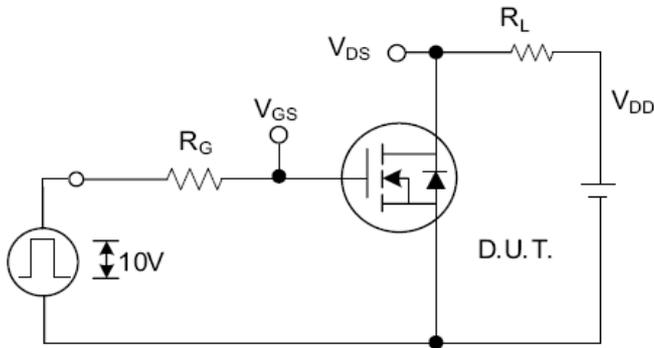


Fig. 2.1 Switching Test Circuit

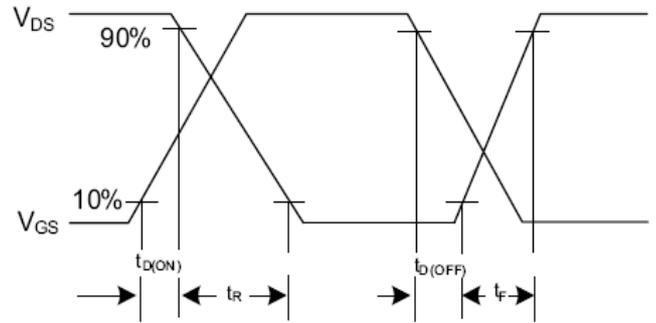


Fig. 2.2 Switching Waveforms

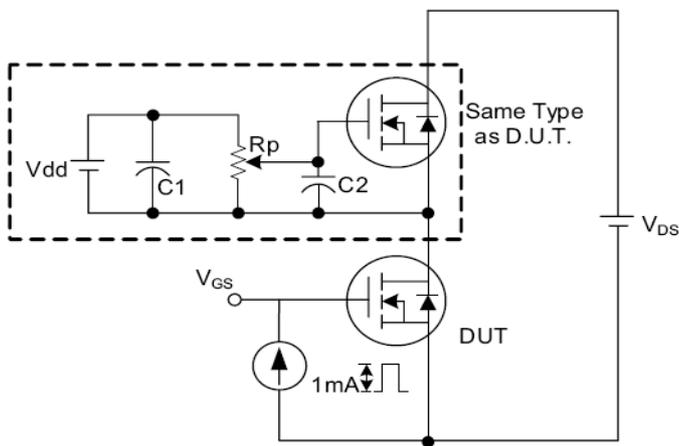


Fig. 3.1 Gate Charge Test Circuit

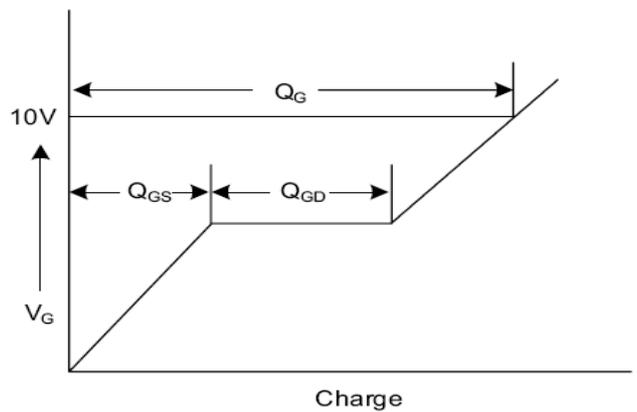


Fig. 3.2 Gate Charge Waveform

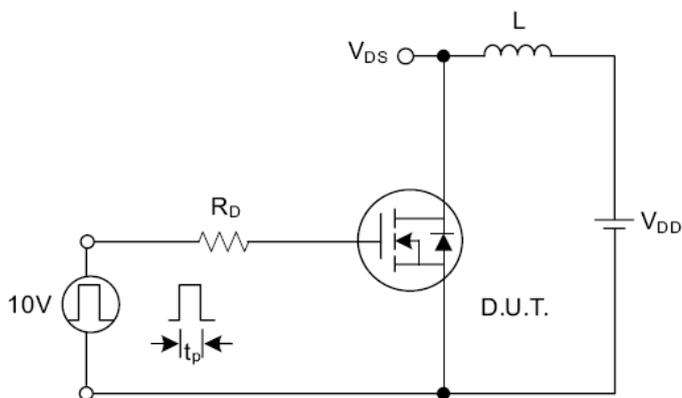


Fig. 4.1 Unclamped Inductive Switching Test Circuit

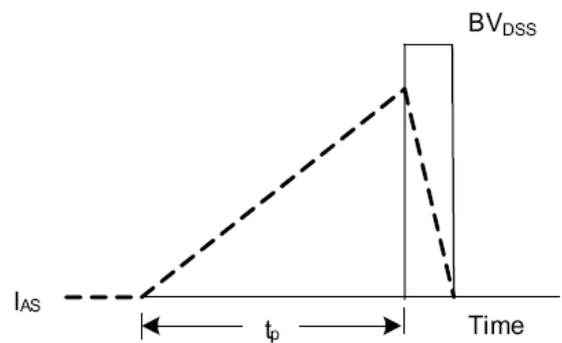


Fig. 4.2 Unclamped Inductive Switching Waveforms



Disclaimers:

Our company reserves the right to make changes without notice in order to improve reliability, function or design and to discontinue any product or service without notice. Customers should obtain the latest relevant information before orders and should verify that such information is current and complete. All products are sold subject to PDW's terms and conditions supplied at the time of order acknowledgement.

Our company warrants performance of its hardware products to the specifications at the time of sale, Testing, reliability and quality control are used to the extent PDW deems necessary to support this warrantee. Except where agreed upon by contractual agreement, testing of all parameters of each product is not necessarily performed.

Our company does not assume any liability arising from the use of any product or circuit designs described herein. Customers are responsible for their products and applications using PDW's components. To minimize risk, customers must provide adequate design and operating safeguards.

Our company does not warrant or convey any license either expressed or implied under its patent rights, nor the rights of others. Reproduction of information in PDW's data sheets or data books is permissible only if reproduction is without modification or alteration. Reproduction of this information with any alteration is an unfair and deceptive business practice. Our company is not responsible or liable for such altered documentation.

Resale of PDW's products with statements different from or beyond the parameters stated by Our company for that product or service voids all express or implied warranties for the associated PDW's product or service and is unfair and deceptive business practice. Our company is not responsible or liable for any such statements.

Life Support Policy:

Our company's products are not authorized for use as critical components in life support devices or systems without the expressed written approval of Our company .

As used herein:

1. Life support devices or systems are devices or systems which:
 - a. are intended for surgical implant into the human body,
 - b. support or sustain life,
 - c. whose failure to perform when properly used in accordance with instructions for used provided in the labeling, can be reasonably expected to result in significant injury to the user.
2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.